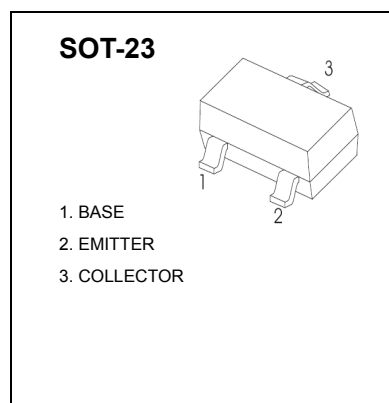


# SOT-23 Plastic-Encapsulate Transistors

## BC807<sup>\*</sup> TRANSISTOR (PNP)

### FEATURE

- Ideally suited for automatic insertion
- Epitaxial planar die construction
- Complementary NPN type available(BC817)



### MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	-50	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-45	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current -Continuous	-0.5	A
P <sub>C</sub>	Collector Power Dissipation	0.3	W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55-150	°C

### ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V <sub>CBO</sub>	I <sub>C</sub> = -10μA, I <sub>E</sub> =0	-50		V
Collector-emitter breakdown voltage	V <sub>CEO</sub>	I <sub>C</sub> = -10mA, I <sub>B</sub> =0	-45		V
Emitter-base breakdown voltage	V <sub>EBO</sub>	I <sub>E</sub> = -1μA, I <sub>C</sub> =0	-5		V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = -45V, I <sub>E</sub> =0		-0.1	μA
Collector cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> = -40V, I <sub>B</sub> =0		-0.2	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -4 V, I <sub>C</sub> =0		-0.1	μA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> = -1V, I <sub>C</sub> = -100mA	100	600	
	h <sub>FE(2)</sub>	V <sub>CE</sub> = -1V, I <sub>C</sub> = -500mA	40		
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-500mA, I <sub>B</sub> = -50mA		-0.7	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA		-1.2	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -10mA f=100MHz	100		MHz

### CLASSIFICATION OF h<sub>FE(1)</sub>

Rank	BC807-16	BC807-25	BC807-40
Range	100-250	160-400	250-600
Marking	5A	5B	5C

# Typical Characteristics

# BC807

